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MOSFET - Power, Single P-Channel, Small Signal -20 V, -127 mA

NTNS2K1P021Z

Features

- Low Profile Ultra Small Package, XDFN3 (0.62 x 0.42 x 0.4 mm) for Extremely Space–Constrained Applications
- -1.5 V Gate Drive
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- High Speed Interfacing
- Level Shift

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

| Parameter | | | Symbol | Value | Unit |
|---|------------------------------|-----------------------|---------------------|---------------|------|
| Drain-to-Source Voltage | | | V _{DSS} 20 | | V |
| Gate-to-Source Volta | Gate-to-Source Voltage | | | ±8 | V |
| Continuous Drain | Steady T _A = 25°C | | I _D | -127 | mA |
| Current (Note 1) | State | T _A = 85°C | | -91 | |
| | t ≤ 5 s | T _A = 25°C | | -146 | |
| Power Dissipation (Note 1) | Steady State | T _A = 25°C | P _D | 125 | mW |
| | t ≤ 5 s | | | 166 | |
| Pulsed Drain Current | t _p = 10 μs | | I _{DM} | -488 | mA |
| Operating Junction and Storage Temperature Range | | | T_J , T_{STG} | –55 to 150 | °C |
| Source Current (Body Diode) (Note 2) | | | Is | 200 | mA |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | | | TL | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.
- 2. Pulse Test: pulse width $\leq 300~\mu s,~duty~cycle \leq 2\%$

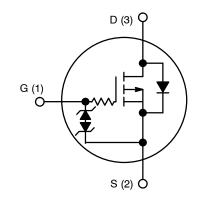


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| V _{(BR)DSS} | R _{DS(on)} MAX | I _D Max |
|----------------------|-------------------------|--------------------|
| | 5.0 Ω @ -4.5 V | |
| -20 V | 7.0 Ω @ –1.8 V | –127 mA |
| | 20 Ω @ -1.2 V | |

P-CHANNEL MOSFET



MARKING DIAGRAM





XDFN3 CASE 711BH

М

= Specific Device Code = Date Code

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------------|--------------------|-----------------------|
| NTNS2K1P021ZTCG | XDFN3 (Pb-Free) | 8000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTNS2K1P021Z

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Max | Unit |
|---|-----------------|-----|------|
| Junction-to-Ambient - Steady State (Note 3) | $R_{\theta JA}$ | 998 | °C/W |
| Junction-to-Ambient - t ≤ 5 s (Note 3) | $R_{\theta JA}$ | 751 | C/VV |

^{3.} Surface–mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise stated)

| Parameter | Symbol | Test Condition | | Min | Тур | Max | Unit |
|---|----------------------|---|-------------------------|------|------|------|------|
| OFF CHARACTERISTICS | I. | | | | I | | |
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | $V_{GS} = 0 \text{ V}, I_D = -25$ | 0 μΑ | -20 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{GS} = 0 \text{ V}, V_{DS} = -5 \text{ V}$ | T _J = 25°C | | | -50 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{GS} = 0 \text{ V}, V_{DS} = -16 \text{ V}$ | T _J = 25°C | | | -100 | nA |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± | 5 V | | | ±100 | nA |
| ON CHARACTERISTICS (Note 4) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | $V_{GS} = V_{DS}, I_D = -25$ | 50 μΑ | -0.4 | | -1.0 | V |
| Drain-to-Source On Resistance | R _{DS(on)} | $V_{GS} = -4.5 \text{ V}, I_D = -100 \text{ mA}$ | | | 2.1 | 5.0 | Ω |
| | | $V_{GS} = -1.8 \text{ V}, I_D = -20 \text{ mA}$ | | | 3.6 | 7.0 | |
| | | $V_{GS} = -1.2 \text{ V}, I_D = -10 \text{ mA}$ | | | 7.3 | 20 | |
| Forward Transconductance | 9 _{FS} | $V_{DS} = -5 \text{ V}, I_D = -125 \text{ mA}$ | | | 0.35 | | S |
| Source-Drain Diode Voltage | V_{SD} | $V_{GS} = 0 \text{ V}, I_{S} = -10 \text{ mA}$ | | | -0.6 | -1.0 | V |
| CHARGES & CAPACITANCES | | | | | | | |
| Input Capacitance | C _{ISS} | | | | 12.8 | | |
| Output Capacitance | C _{OSS} | V _{GS} = 0 V, freq = 1 MHz, \ | √ _{DS} = −15 V | | 2.8 | | pF |
| Reverse Transfer Capacitance | C _{RSS} | | | | 2.0 | | 1 |
| SWITCHING CHARACTERISTICS, VGS = 4.5 V (Note 4) | | | | | | | |
| Turn-On Delay Time | t _{d(ON)} | V_{GS} = -4.5 V, V_{DD} = -15 V, I_{D} = 200 mA, R_{G} = 2 Ω | | | 37 | | |
| Rise Time | t _r | | | | 71 | | ns |
| Turn-Off Delay Time | t _{d(OFF)} | | | | 280 | | |
| Fall Time | t _f | | | | 171 | | |

^{4.} Switching characteristics are independent of operating junction temperatures.

NTNS2K1P021Z

TYPICAL CHARACTERISTICS

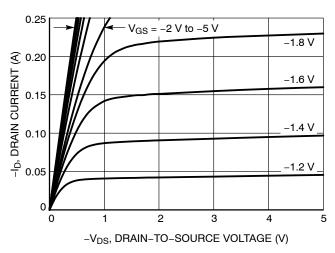


Figure 1. On-Region Characteristics

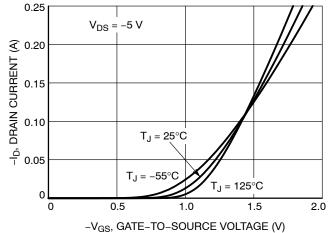


Figure 2. Transfer Characteristics

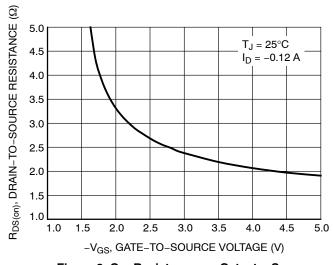


Figure 3. On-Resistance vs. Gate-to-Source Voltage

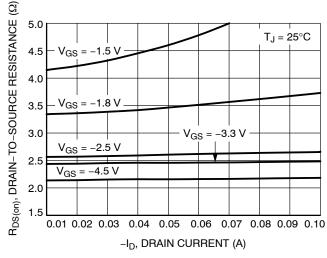


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

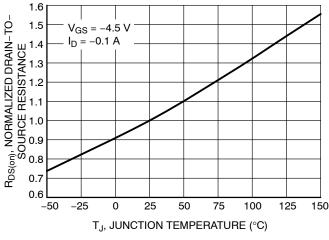


Figure 5. On–Resistance Variation with Temperature

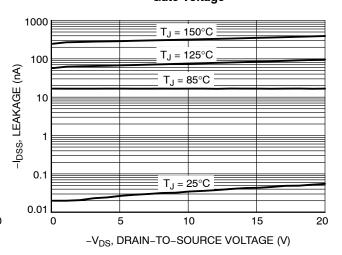


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

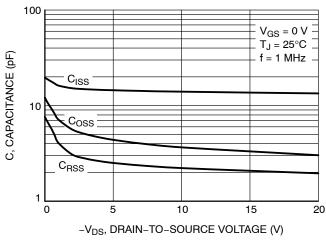


Figure 7. Capacitance Variation

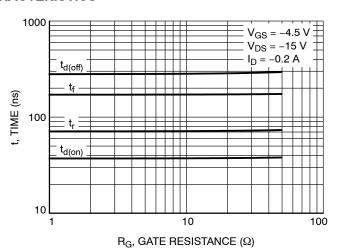


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

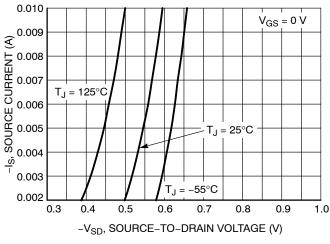


Figure 9. Diode Forward Voltage vs. Current

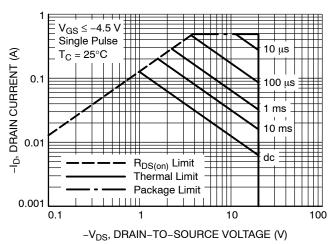


Figure 10. Maximum Rated Forward Biased Safe Operating Area

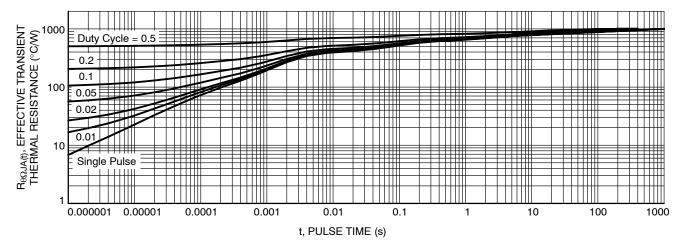
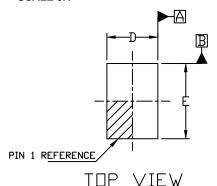


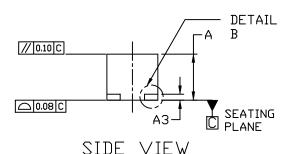
Figure 11. Thermal Response

XDFN3 0.42x0.62, 0.3P CASE 711BH ISSUE A

DATE 29 APR 2018

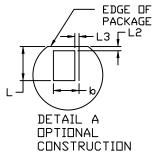






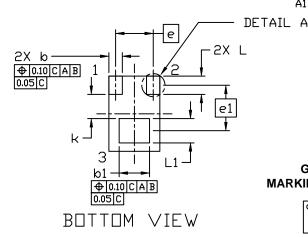
NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 AND 61 APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 0.20 AND 0.25 FROM THE TERMINAL TIP.
- 4. COPLANARITY APPLIES TO THE PLATED TERMINALS.



| | CHINZ LKOC LITHIN | | | |
|------------------|-------------------|-----|---------------------|--|
| L _A : | 3 / | | EXPOSED COPPER | |
| <u> </u> | | _ | MOLDING COMPOUND | |
| ↑ A1- | DETAIL B | CDN | ISTRUCTION | |

| | MILLIMETERS | | | |
|-----|-------------|---------|------|--|
| DIM | MIN. | N□M. | MAX. | |
| Α | 0.33 | 0.38 | 0.43 | |
| A1 | | | 0.07 | |
| A3 | C | .13 REF | | |
| b | 0.05 | 0.11 | 0.17 | |
| b1 | 0.20 | 0.25 | 0.30 | |
| D | 0.32 | 0.42 | 0.52 | |
| Ε | 0.52 | 0.62 | 0.72 | |
| e | 0.30 BSC | | | |
| e1 | 0.38 BCC | | | |
| L | 0.09 | 0.15 | 0.21 | |
| L1 | 0.15 | 0.20 | 0.25 | |
| L2 | | | 0.03 | |
| L3 | | | 0.03 | |
| k | 0.20 REF | | | |
| | | | | |



GENERIC MARKING DIAGRAM*



X = Specific Device CodeM = Date Code

| PACKAGE DUTLINE | <u> </u> | ⊢ 0.35 |
|---------------------------------|--------------|----------------------------------|
| 0.29 0.11 2X 0.21 0.52 | | 0.30 2X 0.25 0.31 PITCH |
| RFCF | IMMFN | DFD |

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| DESCRIPTION: | XDFN3 0.42x0.62, 0.3P | | PAGE 1 OF 1 | |

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